

Abstracts

[Microwave Power GaAs FET Amplifiers](#)

H.Q. Tserng, V. Sokolov, H.M. Macksey and W.R. Wisseman. "Microwave Power GaAs FET Amplifiers." 1976 Transactions on Microwave Theory and Techniques 24.12 (Dec. 1976 [T-MTT] (1976 Symposium Issue)): 936-943.

The development of broad-band microwave amplifiers using state-of-the-art GaAs power FET's covering the 6-12-GHz frequency band is presented. A unique circuit topology incorporating an edge-coupled transmission line section for both impedance matching and input/output dc blocking is described. The microstrip circuit design of an X-band 1-W 22-dB-gain GaAs FET amplifier is also discussed. Microwave performance characteristics such as intermodulation, AM-to-PM conversion, and noise figure are included.

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